imall

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Low Voltage Single Supply Dual DPDT Analog Switch

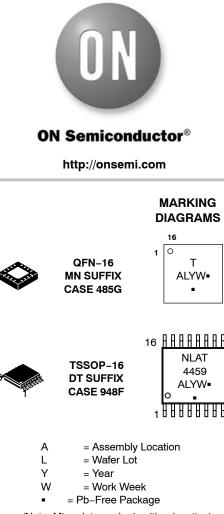
The NLAST44599 is an advanced CMOS dual-independent DPDT (double pole-double throw) analog switch, fabricated with silicon gate CMOS technology. It achieves high-speed propagation delays and low ON resistances while maintaining CMOS low-power dissipation. This DPDT controls analog and digital voltages that may vary across the full power-supply range (from V_{CC} to GND).

The device has been designed so the ON resistance (R_{ON}) is much lower and more linear over input voltage than R_{ON} of typical CMOS analog switches.

The channel-select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The NLAST44599 can also be used as a quad 2-to-1 multiplexerdemultiplexer analog switch with two Select pins that each controls two multiplexer-demultiplexers.

- Select Pins Compatible with TTL Levels
- Channel Select Input Overvoltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break-Before-Make Circuitry
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V; Machine Model > 100 V
- Chip Complexity: 158 FETs
- Pb-Free Packages are Available

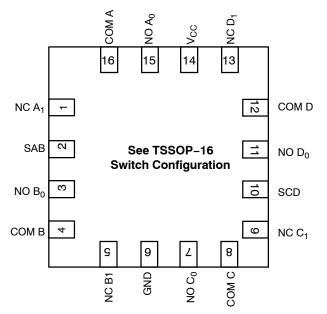


(Note: Microdot may be in either location)

ORDERING INFORMATION

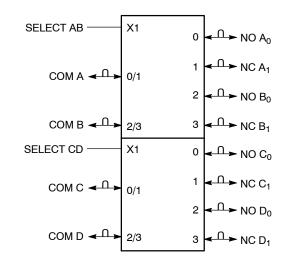
See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

QFN-16 PACKAGE



FUNCTION TABLE

Select AB or CD	ON Channel
LT	NC to COM NO to COM





• NO A₀ 16 1 V_{CC} COM A 2 NC D1 15 NC A₁ 3 COM D 14 LECT AB NO DO 4 13 NO B_0 5 12 SELECT CD COM B 6 11 NC C₁ NC B₁ 7 10 COM C 8 GND 9 NO C₀

TSSOP-16 PACKAGE

Figure 1. Logic Diagram

MAXIMUM RATINGS

Symbol	Par	rameter	Value	Unit
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V
V _{IS}	Analog Input Voltage (V_{NO} or V_{COM})		$-0.5 \le V_{IS} \le V_{CC} \ +0.5$	V
V _{IN}	Digital Select Input Voltage		$-0.5 \leq V_l \leq +7.0$	V
I _{IK}	DC Current, Into or Out of Any Pin		±50	mA
P _D	Power Dissipation in Still Air	QFN-16 TSSOP-16	800 450	mW
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10	260	°C	
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL-94-VO (0.125 in)	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)		2000 100 1000	V
I _{LATCH-UP}	Latch–Up Performance	Above V_{CC} and Below GND at 125°C (Note 4)	±300	mA
θ_{JA}	Thermal Resistance	QFN-16 TSSOP-16	80 164	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A.

2. Tested to EIA/JESD22-A115-A.

3. Tested to JESD22-C101-A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	2.0	5.5	V	
V _{IN}	Digital Select Input Voltage	GND	5.5	V	
V _{IS}	Analog Input Voltage (NC, NO, COM)	GND	V _{CC}	V	
T _A	Operating Temperature Range	- 55	+125	°C	
t _r , t _f	Input Rise or Fall Time, SELECT V _{CC} V _{CC}	= 3.3 V ± 0.3 V = 5.0 V ± 0.5 V	0 0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

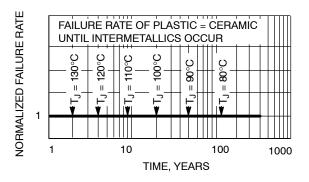


Figure 3. Failure Rate vs. Time Junction Temperature

				Guara			
Symbol	Parameter	Condition	V _{CC}	- 55°C to 25°C	<85°C	<125°C	Unit
V _{IH}	Minimum High-Level Input Voltage, Select Inputs		3.0 4.5 5.5	2.0 2.0 2.0	2.0 2.0 2.0	2.0 2.0 2.0	V
V _{IL}	Maximum Low–Level Input Voltage, Select Inputs		3.0 4.5 5.5	0.5 0.8 0.8	0.5 0.8 0.8	0.5 0.8 0.8	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	5.5	±0.2	±2.0	±2.0	μA
I _{OFF}	Power Off Leakage Current, Select Inputs	V _{IN} = 5.5 V or GND	0	±10	±10	±10	μΑ
I _{CC}	Maximum Quiescent Supply Current	Select and $V_{IS} = V_{CC}$ or GND	5.5	4.0	4.0	8.0	μA

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

DC ELECTRICAL CHARACTERISTICS – Analog Section

				Guarai	nteed Limit	t	
Symbol	Parameter	Condition	Vcc	- 55°C to 25°C	<85°C	<125°C	Unit
R _{ON}	Maximum "ON" Resistance (Figures 17 – 23)	$\begin{split} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{IS} &= GND \text{ to } V_{CC} \\ I_{IN}I &\leq 10.0 \text{ mA} \end{split}$		85 45 30 25	95 50 35 30	105 55 40 35	Ω
R _{FLAT} (ON)	ON Resistance Flatness (Figures 17 – 23)	$\begin{split} & V_{IN} = V_{IL} \text{ or } V_{IH} \\ & I_{IN} I \leq 10.0 \text{ mA} \\ & V_{IS} = 1 \text{ V}, 2 \text{ V}, 3.5 \text{ V} \end{split}$	4.5	4	4	5	Ω
I _{NC(OFF)} I _{NO(OFF)}	NO or NC Off Leakage Current (Figure 9)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{NO} \text{ or } V_{NC} = 1.0 V_{COM} 4.5 V$	5.5	1	10	100	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 9)	$\begin{split} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{NO} \ 1.0 \ V \text{ or } 4.5 \ V \text{ with } V_{NC} \text{ floating or } \\ V_{NO} \ 1.0 \ V \text{ or } 4.5 \ V \text{ with } V_{NO} \text{ floating } \\ V_{COM} &= 1.0 \ V \text{ or } 4.5 \ V \end{split}$	5.5	1	10	100	nA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

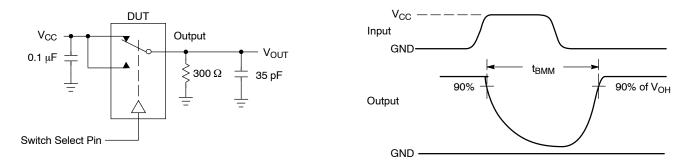
					Guaranteed Maximum Limit							
			v_{cc}	VIS	- 5	5°C to 2	5°C	<8	5°C	<12	25°C	
Symbol	Parameter	Test Conditions	(V)	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
t _{ON}	Turn–On Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	5	23	35	5	38	5	41	ns
	(Figures 12 and 13)	(Figures 5 and 6)	3.0	2.0	5	16	24	5	27	5	30	
			4.5	3.0	2	11	16	2	19	2	22	
			5.5	3.0	2	9	14	2	17	2	20	
t _{OFF}	Turn–Off Time	R_L = 300 Ω , C_L = 35 pF	2.5	2.0	1	7	12	1	15	1	18	ns
	(Figures 12 and 13)	(Figures 5 and 6)	3.0	2.0	1	5	10	1	13	1	16	
			4.5	3.0	1	4	6	1	9	1	12	
			5.5	3.0	1	3	5	1	8	1	11	
t _{BBM}	Minimum Break-Before-Make	V _{IS} = 3.0 V (Figure 4)	2.5	2.0	1	12		1		1		ns
	Time	R_L = 300 Ω , C_L = 35 pF	3.0	2.0	1	11		1		1		
			4.5	3.0	1	6		1		1		
			5.5	3.0	1	5		1		1		

*Typical Characteristics are at 25°C.

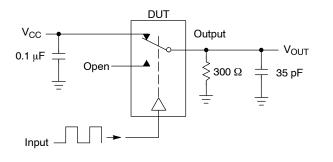
		Typical @ 25, VCC = 5.0 V	
C _{IN}	Maximum Input Capacitance, Select Input	8	pF
C _{NO} or C _{NC}	Analog I/O (Switch Off)	10	
C _{COM}	Common I/O (Switch Off)	10	
C _(ON)	Feedthrough (Switch On)	20	

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			Vcc	Typical	
Symbol	Parameter	Condition	v	25°C	Unit
BW	Maximum On-Channel -3 dB Bandwidth or	V _{IN} = 0 dBm	3.0	145	MHz
	Minimum Frequency Response	V_{IN} centered between V_{CC} and GND	4.5	170	
	(Figure 11)	(Figure 7)	5.5	175	
V _{ONL}	Maximum Feedthrough On Loss	V _{IN} = 0 dBm @ 100 kHz to 50 MHz	3.0	-3	dB
		V_{IN} centered between V_{CC} and GND	4.5	-3	
		(Figure 7)	5.5	-3	
V _{ISO}	Off-Channel Isolation	f = 100 kHz; V _{IS} = 1 V RMS	3.0	-93	dB
	(Figure 10)	V_{IN} centered between V_{CC} and GND	4.5	-93	
		(Figure 7)	5.5	-93	
Q	Charge Injection Select Input to Common I/O	$V_{IN} = V_{CC}$ to GND, $F_{IS} = 20 \text{ kHz}$	3.0	1.5	рС
	(Figure 15)	$t_r = t_f = 3 \text{ ns}$	5.5	3.0	
		$R_{IS} = 0 \ \Omega, \ C_L = 1000 \ pF$			
		$Q = C_L * \Delta V_{OUT}$ (Figure 8)			
THD	Total Harmonic Distortion	$F_{IS} = 20$ Hz to 100 kHz, $R_L = Rgen = 600 \Omega$,			%
	THD + Noise	$C_L = 50 \text{ pF}$			
	(Figure 14)	V _{IS} = 5.0 V _{PP} sine wave	5.5	0.1	
VCT	Channel to Channel Crosstalk	f = 100 kHz; V _{IS} = 1 V RMS			dB
		V_{IN} centered between V_{CC} and GND	5.5	-90	
		(Figure 7)	3.0	-90	







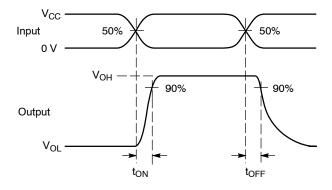
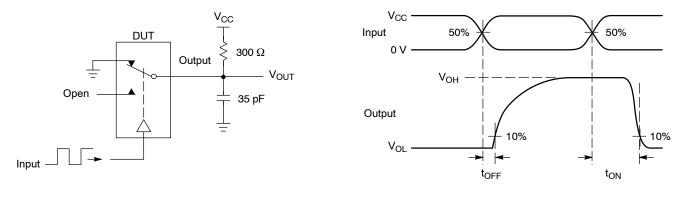
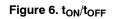
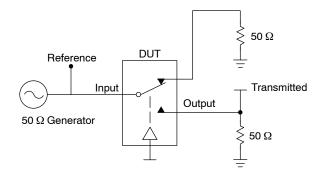


Figure 5. t_{ON}/t_{OFF}



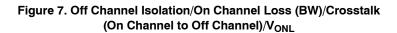


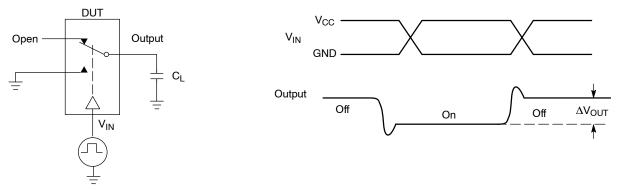


Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} V_{ISO} &= \text{Off Channel Isolation} = 20 \text{ Log } \left(\frac{V_{OUT}}{V_{IN}}\right) & \text{for } V_{IN} \text{ at } 100 \text{ kHz} \\ V_{ONL} &= \text{On Channel Loss} = 20 \text{ Log } \left(\frac{V_{OUT}}{V_{IN}}\right) & \text{for } V_{IN} \text{ at } 100 \text{ kHz} \text{ to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL} V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω







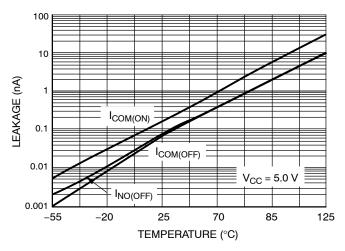
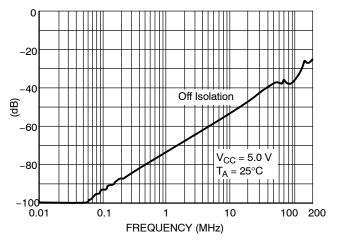
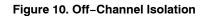


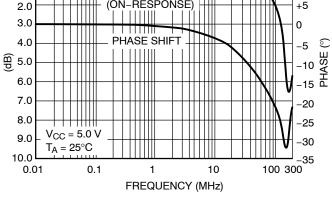
Figure 9. Switch Leakage vs. Temperature

0

1.0







Bandwidth

+15

+10

+5



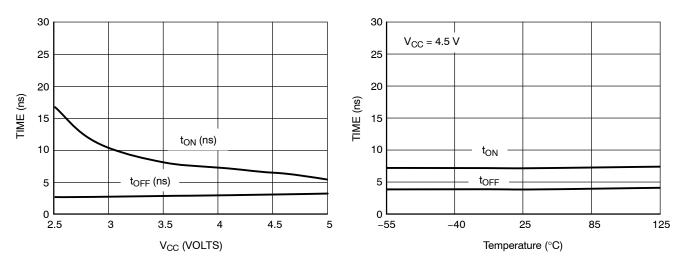
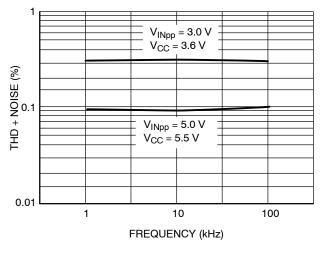


Figure 12. t_{ON} and t_{OFF} vs. V_{CC} at 25°C



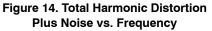
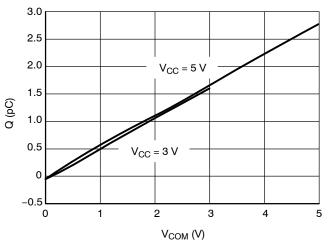
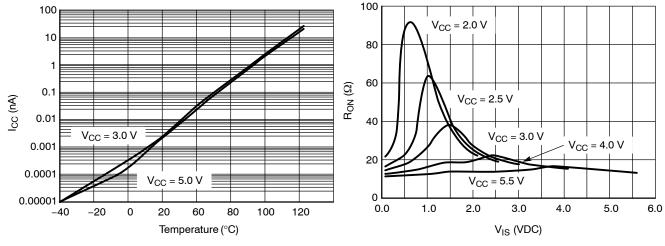


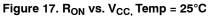
Figure 13. t_{ON} and t_{OFF} vs. Temp











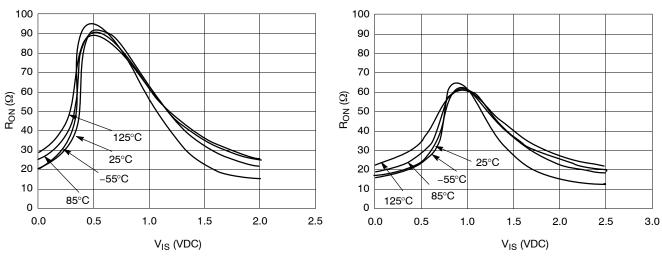


Figure 18. R_{ON} vs Temp, V_{CC} = 2.0 V

Ron (2)

Figure 19. R_{ON} vs. Temp, V_{CC} = 2.5 V

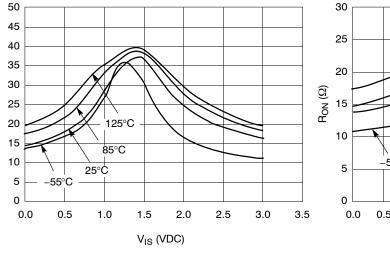


Figure 20. R_{ON} vs. Temp, V_{CC} = 3.0 V

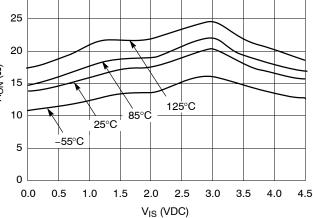


Figure 21. R_{ON} vs. Temp, V_{CC} = 4.5 V

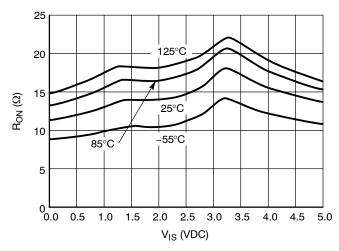


Figure 22. R_{ON} vs. Temp, V_{CC} = 5.0 V

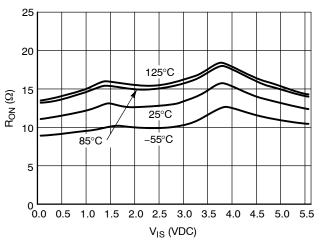


Figure 23. R_{ON} vs. Temp, V_{CC} = 5.5 V

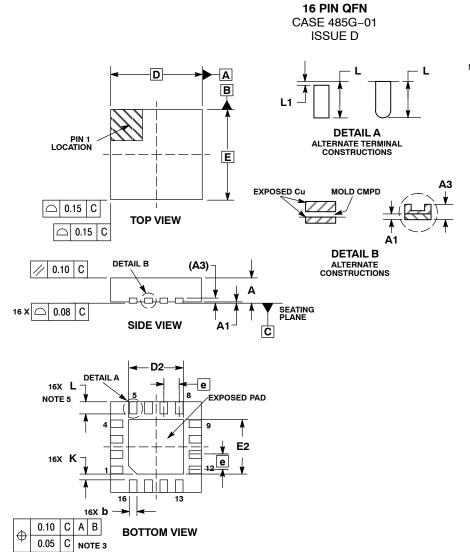
DEVICE ORDERING INFORMATION

		De	vice Nomer				
Device Order Number	Circuit Indicator	Technology	Device Function	Package Suffix	Tape and Reel Suffix	Package Type	Shipping [†]
NLAST44599DT	NL	AS	44599	DT		TSSOP-16*	96 Unit / Rail
NLAST44599DTR2	NL	AS	44599	DT	R2	TSSOP-16*	2500 / Tape & Reel
NLAST44599MN	NL	AS	44599	MN		QFN-16	124 Unit Rail
NLAST44599MNG	NL	AS	44599	MN		QFN-16 (Pb-Free)	124 Unit Rail
NLAST44599MNR2	NL	AS	44599	MN	R2	QFN-16	2500 / Tape & Reel
NLAST44599MNR2G	NL	AS	44599	MN	R2	QFN-16 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

PACKAGE DIMENSIONS

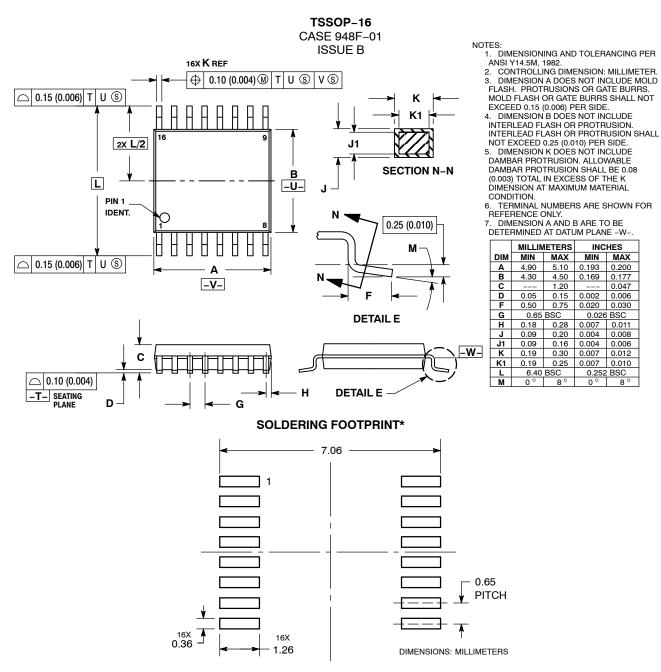


- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
 COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
 L_{max} CONDITION CAN NOT VIOLATE 0.2 MM MINIMUM SPACING BETWEEN LEAD TIP AND FLAG

- AND FLAG

	MILLIN	IETERS		
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
A3	0.20	REF		
b	0.18	0.30		
D	3.00	BSC		
D2	1.65	1.85		
Е	3.00	BSC		
E2	1.65	1.85		
е	0.50	BSC		
К	0.18 TYP			
L	0.30	0.50		
L1	0.00	0.15		

PACKAGE DIMENSIONS



0.008

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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